

MITSUBISHI LASER DIODES
ML9XX40 SERIES

Notice : Some parametric limits are subject to change 2.5Gbps InGaAsP DFB LASER DIODE

**TYPE
NAME**

**ML925B40F / ML920J40S
ML925J40F / ML920L40S**

DESCRIPTION

ML9XX40 series are uncooled DFB (Distributed Feedback) laser diodes for 2.5Gbps transmission emitting light beam at 1470~1610nm. $\lambda/4$ shifted grating structure is employed to obtain excellent SMSR performance under 2.5Gbps modulation. Furthermore, ML9xx40 can operate in the wide temperature range from 0°C to 85 °C without any temperature control. They are well suited for light source in long distance digital transmission application of coarse WDM.

APPLICATION

- 2.5Gbps long-haul transmission
- Coarse WDM application

FEATURES

- $\lambda/4$ shifted grating structure
- Wide temperature range operation (0°C to 85°C)
- High side-mode-suppression-ratio (typical 45dB)
- High resonance frequency (typical 11GHz)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Unit
Po	Output power	CW	6	mW
If	Forward current (Laser diode)	---	150	mA
V _{RL}	Reverse voltage (Laser diode)	---	2	V
I _{FD}	Forward current (Photo diode)	---	2	mA
V _{RD}	Reverse voltage (Photo diode)	---	20	V
Tc	Case temperature	---	0 to +85	°C
Tstg	Storage temperature	---	-40 to +100	°C

ELECTRICAL/OPTICAL CHARACTERISTICS (Tc=25°C)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I _{th}	Threshold current	CW	---	10	15	mA
		CW	<*1>	35	40	
		Tc=85°C	<*2>	45	50	
I _{op}	Operation current	CW, Po=5mW	---	35	45	mA
		CW, Po=5mW	<*1>	70	80	
		Tc=85°C	<*2>	90	100	
V _{op}	Operating voltage	CW, Po=5mW	---	1.1	1.5	V
η	Slope efficiency	CW, Po=5mW	0.17	0.22	---	mW/mA
		CW, Po=5mW <*3>	0.15	0.20	---	
λ_p	Peak wavelength	CW, Po=5mW	<*4>, <*5>			nm
SMSR	Side mode suppression ratio	CW, Po=5mW, Tc=0 to 85°C	35	45	---	dB
	Side mode suppression ratio(RF)	2.48832Gbps, I _b =I _{th} , I _{pp} =40mA	---	45	---	
$\theta_{//}$	Beam divergence angle (parallel) <*6>	CW, Po=5mW	---	25	---	deg.
θ_{\perp}	(perpendicular) <*6>	CW, Po=5mW	---	30	---	deg.
f _r	Resonance frequency	2.48832Gbps, I _b =I _{th} , I _{pp} =40mA	---	11	---	GHz
t _r , t _f	Rise and Fall time <*7>	2.48832Gbps, I _b =I _{th} , I _{pp} =40mA 20%-80%	---	80	120	ps
I _m	Monitoring output current (PD)	CW, Po=5mW, V _{RD} =1V, R _L =10 Ω	0.1	---	1.0	mA
I _d	Dark current (PD)	V _{RD} =5V	---	---	0.1	μ A
C _t	Capacitance (PD)	V _{RD} =5V	---	10	20	pF

<*1> Applied to ML9xx40-04~09 and -12~17.

<*2> Applied to ML9xx40-10~11 and -18~19.

<*3> Applied to ML925J40F and ML920L40S.

<*6> Beam divergence is not applied to ML925J40F and ML920L40S.

<*7> Except influence of the 18mm lead.

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<*4> Peak Wavelength

Type	Symbol	Test Condition	Limits			Unit
			Min.	Typ.	Max.	
ML925B40F-01 / ML920J40S-01 ML925J40F-01 / ML920L40S-01	λ_p	CW, Po=5mW Tc= 0 to 85°C	1530	1550	1570	nm
ML925B40F-04 / ML920J40S-04 ML925J40F-04 / ML920L40S-04		CW, Po=5mW Tc= 25°C	1467	1470	1473	
ML925B40F-05 / ML920J40S-05 ML925J40F-05 / ML920L40S-05			1487	1490	1493	
ML925B40F-06 / ML920J40S-06 ML925J40F-06 / ML920L40S-06			1507	1510	1513	
ML925B40F-07 / ML920J40S-07 ML925J40F-07 / ML920L40S-07			1527	1530	1533	
ML925B40F-08 / ML920J40S-08 ML925J40F-08 / ML920L40S-08			1547	1550	1553	
ML925B40F-09 / ML920J40S-09 ML925J40F-09 / ML920L40S-09			1567	1570	1573	
ML925B40F-10 / ML920J40S-10 ML925J40F-10 / ML920L40S-10			1587	1590	1593	
ML925B40F-11 / ML920J40S-11 ML925J40F-11 / ML920L40S-11			1607	1610	1613	

<*5> Peak Wavelength


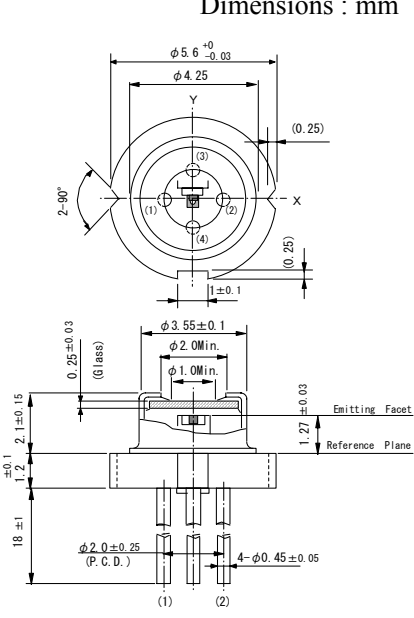
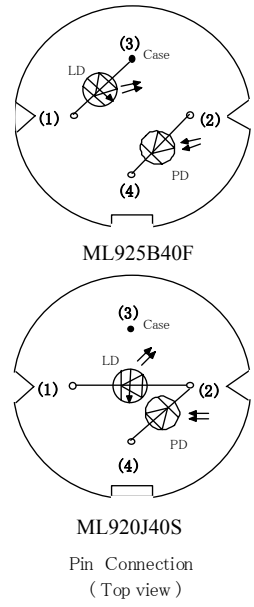
Type	Symbol	Test Condition	Limits			Unit
			Min.	Typ.	Max.	
ML925B40F-12 / ML920J40S-12 ML925J40F-12 / ML920L40S-12	λ_p	CW, Po=5mW Tc= 25°C	1468	1470	1472	nm
ML925B40F-13 / ML920J40S-13 ML925J40F-13 / ML920L40S-13			1488	1490	1492	
ML925B40F-14 / ML920J40S-14 ML925J40F-14 / ML920L40S-14			1508	1510	1512	
ML925B40F-15 / ML920J40S-15 ML925J40F-15 / ML920L40S-15			1528	1530	1532	
ML925B40F-16 / ML920J40S-16 ML925J40F-16 / ML920L40S-16			1548	1550	1552	
ML925B40F-17 / ML920J40S-17 ML925J40F-17 / ML920L40S-17			1568	1570	1572	
ML925B40F-18 / ML920J40S-18 ML925J40F-18 / ML920L40S-18			1588	1590	1592	
ML925B40F-19 / ML920J40S-19 ML925J40F-19 / ML920L40S-19			1608	1610	1612	


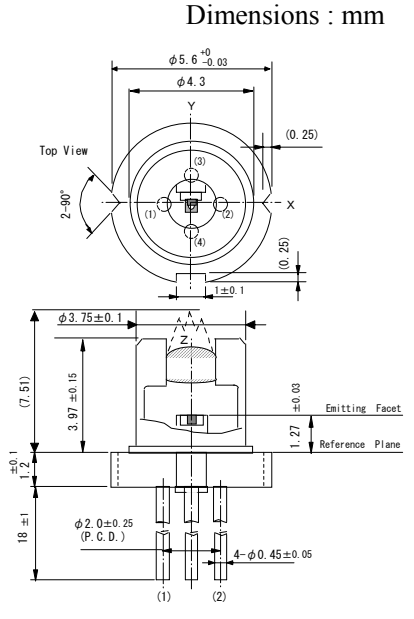
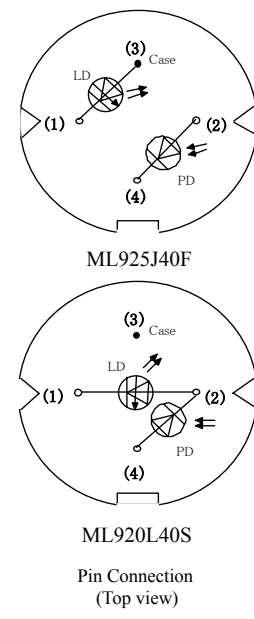
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OUTLINE DRAWINGS

<p>ML925B40F ML920J40S</p> 	<p>Dimensions : mm</p>  <p>Top View: $\phi 5.6^{+0}_{-0.03}$, $\phi 4.25$, Y, $2-90^\circ$, X, 0.25, 1 ± 0.1, 0.25 ± 0.03 (Glass), $\phi 3.55 \pm 0.1$, $\phi 2.0 \text{ Min.}$, $\phi 1.0 \text{ Min.}$, 1.27 ± 0.03 (Emitting Facet), 1.27 (Reference Plane), 18 ± 1, $\phi 2.0 \pm 0.25$ (P.C.D.), $4-\phi 0.45 \pm 0.05$, 1 ± 0.1, ± 0.1, 1.2, 2.1 ± 0.15</p> <p>Side View: 1.27 ± 0.03 (Emitting Facet), 1.27 (Reference Plane), 18 ± 1, $\phi 2.0 \pm 0.25$ (P.C.D.), $4-\phi 0.45 \pm 0.05$, 1 ± 0.1, ± 0.1, 1.2, 2.1 ± 0.15</p>	 <p>ML925B40F</p> <p>ML920J40S</p> <p>Pin Connection (Top view)</p>
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<p>ML925J40F ML920L40S</p> 	<p>Dimensions : mm</p>  <p>Top View: $\phi 5.6^{+0}_{-0.03}$, $\phi 4.3$, Y, $2-90^\circ$, X, 0.25, 1 ± 0.1, 0.25 ± 0.03 (Glass), $\phi 3.75 \pm 0.1$, $\phi 2.0 \text{ Min.}$, $\phi 1.0 \text{ Min.}$, 1.27 ± 0.03 (Emitting Facet), 1.27 (Reference Plane), 18 ± 1, $\phi 2.0 \pm 0.25$ (P.C.D.), $4-\phi 0.45 \pm 0.05$, 1 ± 0.1, ± 0.1, 1.2, 7.51, 3.97 ± 0.15</p> <p>Side View: 1.27 ± 0.03 (Emitting Facet), 1.27 (Reference Plane), 18 ± 1, $\phi 2.0 \pm 0.25$ (P.C.D.), $4-\phi 0.45 \pm 0.05$, 1 ± 0.1, ± 0.1, 1.2, 7.51, 3.97 ± 0.15</p>	 <p>ML925J40F</p> <p>ML920L40S</p> <p>Pin Connection (Top view)</p>
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